

REMARKS

Claims 1-12 are active in the present application. Claims 4-6 and 10-12 have been amended to remove multiple dependencies. No new matter is added. An action on the merits and allowance of claims is solicited.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Norman F. Oblon
Attorney of Record
Registration No. 24,618

Daniel J. Pereira, Ph.D.
Registration No. 45,518



22850

(703) 413-3000
Fax #: (703)413-2220
DJPER/kst

I:\atty\SUKOS\214810us-pr.wpd

Marked-Up Copy

Serial No:

Amendment Filed on:

12-27-01

IN THE CLAIMS

--4. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 3] claim 1,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

5. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 4] claim 1,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

6. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 1 to 5] claim 1,

wherein said conductor is formed in a region up to the position of 60% in a thickness-direction from the face opposite to a wafer treating face of said ceramic substrate.

10. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 9] claim 7,

wherein a conductor is formed on the face opposite to a wafer treating face.

11. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 10] claim 7,

wherein said ceramic substrate is used in a temperature range of 100 to 700°C.

12. (Amended) The ceramic substrate for a semiconductor-producing/examining device according to [any of claims 7 to 11] claim 7,

wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.--

0926296.122701